

# Hadis MorkoÃ§

## List of Publications by Year in descending order

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154  
papers

7,538  
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53230

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g-index

191  
all docs

191  
docs citations

191  
times ranked

7204  
citing authors

#	ARTICLE	IF	CITATIONS
1	Luminescence properties of defects in GaN. Journal of Applied Physics, 2005, 97, 061301.	2.5	1,664
2	ZnO Devices and Applications: A Review of Current Status and Future Prospects. Proceedings of the IEEE, 2010, 98, 1255-1268.	21.3	669
3	Very low resistance multilayer Ohmic contact to n-GaN. Applied Physics Letters, 1996, 68, 1672-1674.	3.3	436
4	Comprehensive analysis of Si-doped Al <sub>x</sub> Ga <sub>1-x</sub> As (x=0 to 1): Theory and experiments. Physical Review B, 1984, 30, 4481-4492.	3.2	398
5	Microwave ferrites, part 1: fundamental properties. Journal of Materials Science: Materials in Electronics, 2009, 20, 789-834.	2.2	348
6	On the efficiency droop in InGaN multiple quantum well blue light emitting diodes and its reduction with p-doped quantum well barriers. Applied Physics Letters, 2008, 93, .	3.3	301
7	Reduction of efficiency droop in InGaN light emitting diodes by coupled quantum wells. Applied Physics Letters, 2008, 93, .	3.3	208
8	Doping Asymmetry Problem in ZnO: Current Status and Outlook. Proceedings of the IEEE, 2010, 98, 1269-1280.	21.3	179
9	GaN-based modulation doped FETs and UV detectors. Solid-State Electronics, 2002, 46, 157-202.	1.4	153
10	Electron density of the two-dimensional electron gas in modulation doped layers. Journal of Applied Physics, 1983, 54, 2093-2096.	2.5	131
11	Energy band bowing parameter in Al <sub>x</sub> Ga <sub>1-x</sub> N alloys. Journal of Applied Physics, 2002, 92, 4837-4839.	2.5	120
12	Microwave ferrites, part 2: passive components and electrical tuning. Journal of Materials Science: Materials in Electronics, 2009, 20, 911-952.	2.2	110
13	Recombination dynamics of free and localized excitons in GaN/Ga <sub>0.93</sub> Al <sub>0.07</sub> N quantum wells. Physical Review B, 1998, 57, R9447-R9450.	3.2	109
14	High electron mobility in nearly lattice-matched AlInN/AlN/GaN heterostructure field effect transistors. Applied Physics Letters, 2007, 91, 132116.	3.3	107
15	GaN-Based Light-Emitting Diodes: Efficiency at High Injection Levels. Proceedings of the IEEE, 2010, 98, 1180-1196.	21.3	103
16	Polarization effects in nitride semiconductor device structures and performance of modulation doped field effect transistors. Solid-State Electronics, 1999, 43, 1909-1927.	1.4	102
17	Recent Development of Boron Nitride towards Electronic Applications. Advanced Electronic Materials, 2017, 3, 1600485.	5.1	98
18	Collector-emitter offset voltage in AlGaAs/GaAs heterojunction bipolar transistors. Applied Physics Letters, 1985, 47, 313-315.	3.3	93

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19	Oscillator strengths for optical band-to-band processes in GaN epilayers. <i>Physical Review B</i> , 1996, 54, 7678-7681.	3.2	81
20	Theoretical investigation of electrical characteristics of AlGaIn/GaN modulation doped field-effect transistors. <i>Journal of Applied Physics</i> , 1996, 80, 3031-3042.	2.5	78
21	Systematic measurement of Al <sub>x</sub> Ga <sub>1-x</sub> N refractive indices. <i>Applied Physics Letters</i> , 2001, 79, 4103-4105.	3.3	77
22	High- $\epsilon_r$ dielectrics and advanced channel concepts for Si MOSFET. <i>Journal of Materials Science: Materials in Electronics</i> , 2008, 19, 915-951.	2.2	73
23	Carrier dynamics in bulk GaN. <i>Journal of Applied Physics</i> , 2012, 111, .	2.5	65
24	Small Signal Equivalent Circuit Modeling for AlGaIn/GaN HFET: Hybrid Extraction Method for Determining Circuit Elements of AlGaIn/GaN HFET. <i>Proceedings of the IEEE</i> , 2010, 98, 1140-1150.	21.3	63
25	GaN epitaxy on thermally treated c-plane bulk ZnO substrates with O and Zn faces. <i>Applied Physics Letters</i> , 2004, 84, 2268-2270.	3.3	62
26	Dielectric functions and electronic band structure of lead zirconate titanate thin films. <i>Journal of Applied Physics</i> , 2005, 98, 094108.	2.5	62
27	Photoluminescence characterization of the quantum well structure and influence of optical illumination on the electrical performance of AlGaIn/GaN modulation-doped field-effect transistors. <i>Applied Physics Letters</i> , 1996, 69, 1420-1422.	3.3	59
28	High-purity GaAs and Cr-doped GaAs epitaxial layers by MBE. <i>Journal of Applied Physics</i> , 1979, 50, 6413-6416.	2.5	57
29	Suppression of leakage currents and their effect on the electrical performance of AlGaIn/GaN modulation doped field-effect transistors. <i>Applied Physics Letters</i> , 1996, 69, 1229-1231.	3.3	53
30	Electrical conduction in silicon nitrides deposited by plasma enhanced chemical vapour deposition. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 1996, 73, 723-736.	0.6	51
31	Photoreflectance investigations of the bowing parameter in AlGaIn alloys lattice-matched to GaN. <i>Applied Physics Letters</i> , 1999, 74, 3353-3355.	3.3	49
32	Bulk ZnO: Current Status, Challenges, and Prospects. <i>Proceedings of the IEEE</i> , 2010, 98, 1339-1350.	21.3	43
33	Surface band bending in as-grown and plasma-treated n-type GaN films using surface potential electric force microscopy. <i>Applied Physics Letters</i> , 2004, 84, 3070-3072.	3.3	42
34	Transport properties of Sn-doped Al <sub>x</sub> Ga <sub>1-x</sub> As grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1980, 51, 4882-4884.	2.5	40
35	Fabrication and current-voltage characterization of a ferroelectric lead zirconate titanate/AlGaIn-GaN field effect transistor. <i>Applied Physics Letters</i> , 2006, 88, 123508.	3.3	40
36	Status of Growth of Group III-Nitride Heterostructures for Deep Ultraviolet Light-Emitting Diodes. <i>Crystals</i> , 2017, 7, 300.	2.2	39

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37	In situ transmission electron microscopy of AlN growth by nitridation of (0001) $\text{Al}_2\text{O}_3$ . Journal of Applied Physics, 1998, 83, 2847-2850.	2.5	38
38	InGaN light-emitting diodes: Efficiency-limiting processes at high injection. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, .	2.1	38
39	Metal-insulator-semiconductor structures on $\text{p}^+\text{-GaAs}$ with low interface state density. Applied Physics Letters, 1996, 69, 230-232.	3.3	37
40	Temperature dependence of current gain in AlGaAs/GaAs heterojunction bipolar transistors. Applied Physics Letters, 1984, 45, 1086-1088.	3.3	36
41	An alternative material for transparent antennas for commercial and medical applications. Microwave and Optical Technology Letters, 2017, 59, 773-777.	1.4	34
42	Cathodoluminescence measurement of an orientation dependent aluminum concentration in $\text{Al}_x\text{Ga}_{1-x}\text{As}$ epilayers grown by molecular beam epitaxy on a nonplanar substrate. Applied Physics Letters, 1989, 54, 1347-1349.	3.3	33
43	III-Nitride semiconductor growth by MBE: Recent issues. Journal of Materials Science: Materials in Electronics, 2001, 12, 677-695.	2.2	33
44	Status of Reliability of GaN-Based Heterojunction Field Effect Transistors. Proceedings of the IEEE, 2010, 98, 1127-1139.	21.3	31
45	Experimental study of the frequency limits of a resonant tunneling oscillator. Applied Physics Letters, 1986, 48, 422-424.	3.3	30
46	Properties of GaAs on Si grown by molecular beam epitaxy. Critical Reviews in Solid State and Materials Sciences, 1990, 16, 91-114.	12.3	30
47	Structural and electrical properties of $\text{Pb}(\text{Zr,Ti})\text{O}_3$ grown on (0001) GaN using a double $\text{PbTiO}_3\text{-PbO}$ bridge layer. Applied Physics Letters, 2007, 91, .	3.3	29
48	Purity of GaAs grown by LPE in a graphite boat. Journal of Crystal Growth, 1976, 36, 109-114.	1.5	28
49	Ti/Al/Ni/Au Ohmic contacts for AlInN/AlN/GaN-based heterojunction field-effect transistors. Journal of Applied Physics, 2010, 107, .	2.5	28
50	Large pyroelectric effect in undoped epitaxial $\text{Pb}(\text{Zr,Ti})\text{O}_3$ thin films on $\text{SrTiO}_3$ substrates. Applied Physics Letters, 2008, 93, 052913.	3.3	27
51	Ferromagnetism in ZnO- and GaN-Based Diluted Magnetic Semiconductors: Achievements and Challenges. Proceedings of the IEEE, 2010, 98, 1288-1301.	21.3	26
52	Resonant surface plasmon-induced modification of photoluminescence from GaN/AlN quantum dots. Nanotechnology, 2004, 15, 1252-1255.	2.6	25
53	Chromium and tellurium redistribution in GaAs and $\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}$ grown by molecular beam epitaxy. Journal of Applied Physics, 1980, 51, 5986-5991.	2.5	23
54	GROWTH, STRUCTURES, AND OPTICAL PROPERTIES OF III-NITRIDE QUANTUM DOTS. International Journal of High Speed Electronics and Systems, 2002, 12, 79-110.	0.7	21

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55	Defect reduction in GaN epilayers grown by metal-organic chemical vapor deposition with in situ SiNx nanonetwork. Applied Physics Letters, 2007, 90, 262112.	3.3	21
56	Low-Frequency Noise Measurements of AlGaIn/GaN Metal&#x2013;Oxide&#x2013;Semiconductor Heterostructure Field-Effect Transistors With HfAlO Gate Dielectric. IEEE Electron Device Letters, 2010, 31, 1041-1043.	3.9	21
57	High quality epitaxial growth of PbTiO3 by molecular beam epitaxy using H2O2 as the oxygen source. Applied Physics Letters, 2006, 89, 122912.	3.3	19
58	Field-assisted emission in AlGaIn/GaN heterostructure field-effect transistors using low-frequency noise technique. Journal of Applied Physics, 2011, 109, .	2.5	19
59	Polarity control and residual strain in ZnO epilayers grown by molecular beam epitaxy on (0001) GaN/sapphire. Physica Status Solidi - Rapid Research Letters, 2016, 10, 682-686.	2.4	19
60	ApnpAlGaAs/GaAs heterojunction bipolar transistor. Applied Physics Letters, 1985, 46, 302-304.	3.3	18
61	Large electro-optic effect in single-crystal Pb(Zr,Ti)O3 (001) measured by spectroscopic ellipsometry. Journal of Applied Physics, 2008, 104, 093103.	2.5	18
62	Polarization effects in nitride semiconductors and device structures. Materials Research Innovations, 1999, 3, 97-106.	2.3	17
63	Epitaxial growth of (001)-oriented Ba0.5Sr0.5TiO3 thin films on a-plane sapphire with an MgO/ZnO bridge layer. Applied Physics Letters, 2009, 95, 212901.	3.3	17
64	Effect of carrier spillover and Auger recombination on the efficiency droop in InGaIn-based blue LEDs. Superlattices and Microstructures, 2010, 47, 118-122.	3.1	17
65	Zinc Oxide Materials and Devices Grown by Molecular Beam Epitaxy. , 2018, , 343-375.		17
66	Visible-ultraviolet spectroscopic ellipsometry of lead zirconate titanate thin films. Applied Physics Letters, 2005, 86, 262902.	3.3	16
67	Infrared optical absorbance of intersubband transitions in GaN/AlGaIn multiple quantum well structures. Journal of Applied Physics, 2003, 93, 10140-10142.	2.5	15
68	Effect of large strain on dielectric and ferroelectric properties of Ba0.5Sr0.5TiO3 thin films. Applied Physics Letters, 2009, 95, 012907.	3.3	15
69	I-V characteristics of Au&#x2013;Ni Schottky diodes on GaN with SiNx nanonetwork. Applied Physics Letters, 2006, 89, 152108.	3.3	14
70	The Growth of Uniform Submicron GaAs Layers by Liquid Phase Epitaxy. Journal of the Electrochemical Society, 1976, 123, 906-912.	2.9	13
71	Enhanced microwave dielectric tunability of Ba0.5Sr0.5TiO3 thin films grown with reduced strain on DyScO3 substrates by three-step technique. Journal of Applied Physics, 2013, 113, 044108.	2.5	13
72	Interface properties of Si<sub>3</sub>N<sub>4</sub>/Si/n-GaAs metal-insulator-semiconductor structure using a Si interlayer. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1996, 74, 219-234.	0.6	12

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73	Minority-carrier characteristics of SiN <sub>x</sub> /GaAs metal-insulator-semiconductor structures with Si/Ge interlayers. Applied Physics Letters, 1997, 71, 1210-1212.	3.3	12
74	Proposed explanation of the anomalous doping characteristics of III-V nitrides. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1997, 76, 131-143.	0.6	12
75	Stimulated emission and ultrafast carrier relaxation in AlGa <sub>N</sub> /Ga <sub>N</sub> multiple quantum wells. Applied Physics Letters, 2003, 82, 4080-4082.	3.3	12
76	Near-infrared wavelength intersubband transitions in GaN/AlN short period superlattices. Applied Physics Letters, 2006, 89, 1511-1512.	3.3	12
77	Improvement of optical quality of semipolar (112̄) GaN on m-plane sapphire by in-situ epitaxial lateral overgrowth. Journal of Applied Physics, 2016, 119, .	2.5	12
78	Group III Nitrides. Springer Handbooks, 2017, , 1-1.	0.6	12
79	Saga of efficiency degradation at high injection in InGa <sub>N</sub> light emitting diodes. Turkish Journal of Physics, 2014, 38, 269-313.	1.1	11
80	Hot phonons in InAlN/AlN/GaN heterostructure 2DEG channels. Proceedings of SPIE, 2009, , .	0.8	10
81	Thickness Variations and Absence of Lateral Compositional Fluctuations in Aberration-Corrected STEM Images of InGa <sub>N</sub> LED Active Regions at Low Dose. Microscopy and Microanalysis, 2014, 20, 864-868.	0.4	10
82	High-Performance BeMgZnO/ZnO Heterostructure Field-Effect Transistors. Physica Status Solidi - Rapid Research Letters, 2020, 14, 2000371.	2.4	10
83	Characteristics of Si <sub>3</sub> N <sub>4</sub> /Si/n-GaAs metal-insulator-semiconductor interfaces grown on GaAs(111)B substrate. Applied Physics Letters, 1996, 69, 3025-3027.	3.3	9
84	Generation-recombination noise in gallium nitride-based quantum well structures. Journal of Applied Physics, 2003, 93, 5337-5345.	2.5	9
85	Characterization of Ag Schottky Barriers on Be <sub>0.02</sub> Mg <sub>0.26</sub> ZnO/ZnO Heterostructures. Physica Status Solidi - Rapid Research Letters, 2018, 12, 1700366.	2.4	9
86	A Platform for Complementary Metal-Oxide-Semiconductor Compatible Plasmonics: High Plasmonic Quality Titanium Nitride Thin Films on Si (001) with a MgO Interlayer. Advanced Photonics Research, 2021, 2, 2000210.	3.6	8
87	Measurement of the minority-carrier lifetime and injection efficiency in AlGaAs/GaAs heterojunction bipolar transistors. Applied Physics Letters, 1986, 48, 367-369.	3.3	6
88	Si <sub>3</sub> N <sub>4</sub> /Si/In <sub>0.05</sub> Ga <sub>0.95</sub> As/n-GaAs metal-insulator-semiconductor devices. Journal of Applied Physics, 1997, 81, 516-523.	2.5	6
89	<title>Megahertz bandwidth Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN-based p-i-n detectors</title>. , 1998, 3287, 198.		6
90	POLARIZATION EFFECTS IN NITRIDE SEMICONDUCTOR HETEROSTRUCTURES. International Journal of High Speed Electronics and Systems, 2000, 10, 25-37.	0.7	6

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91	Photoluminescence of Mg-doped <i>m</i> -plane GaN grown by MOCVD on bulk GaN substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011, 208, 1532-1534.	1.8	6
92	Measurements of generation-recombination effect by low-frequency phase-noise technique in AlGaIn/GaN MOSFETs. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 1539-1543.	0.8	6
93	Indium-incorporation efficiency in semipolar (11-22) oriented InGaIn-based light emitting diodes. , 2015, , .		6
94	Influence of ZnO thin film crystallinity on <i>in vitro</i> biocompatibility. <i>Toxicology Research</i> , 2018, 7, 754-759.	2.1	6
95	Microstructure and field mapping of AlInN-based heterostructures and devices. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 2436-2439.	0.8	5
96	Polarity Control within One Monolayer at ZnO/GaN Heterointerface: (0001) Plane Inversion Domain Boundary. <i>ACS Applied Materials &amp; Interfaces</i> , 2018, 10, 37651-37660.	8.0	5
97	Modulation Doped Al <sub>x</sub> Ga <sub>1-x</sub> As/GaAs Field Effect Transistors (MODFETS): Analysis, Fabrication and Performance. , 1985, , 625-676.		5
98	Metal-insulator-semiconductor structure on GaAs using a pseudomorphic Si/GaP interlayer. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1997, 15, 252.	1.6	4
99	Characteristics of Si <sub>3</sub> N <sub>4</sub> /GaAs metal-Insulator-semiconductor interfaces with coherent Si/Al <sub>0.3</sub> Ga <sub>0.7</sub> As interlayers. <i>Journal of Electronic Materials</i> , 1997, 26, 1076-1082.	2.2	4
100	Structural and Optical Properties of PbTiO <sub>3</sub> Grown on SrTiO <sub>3</sub> Substrates by Peroxide MBE. <i>Materials Research Society Symposia Proceedings</i> , 2006, 966, 1.	0.1	4
101	Reduction of Flicker Noise in AlGaIn/GaN-Based HFETs After High Electric-Field Stress. <i>IEEE Electron Device Letters</i> , 2011, 32, 1513-1515.	3.9	4
102	Carrier dynamics under two- and single-photon excitation in bulk GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2012, 249, 503-506.	1.5	4
103	High-Quality Plasmonic Materials TiN and ZnO:Al by Atomic Layer Deposition. <i>Physica Status Solidi - Rapid Research Letters</i> , 2021, 15, 2100227.	2.4	4
104	Group III Nitrides. , 2006, , 753-804.		4
105	Effects of Rapid Thermal Annealing Treatment on the Surface Band Bending of n-type GaN Studied by Surface Potential Electric Force Microscopy. <i>Materials Science Forum</i> , 2006, 527-529, 1529-1532.	0.3	3
106	Epitaxial growth of ZrO <sub>2</sub> on GaN templates by oxide molecular beam epitaxy. <i>Applied Physics Letters</i> , 2007, 91, 022916.	3.3	3
107	Studies of III-Nitride Superlattice Structures Implanted with Lanthanide Ions. <i>Materials Research Society Symposia Proceedings</i> , 2008, 1111, 1.	0.1	3
108	Active region dimensionality and quantum efficiencies of InGaIn LEDs from temperature dependent photoluminescence transients. <i>Proceedings of SPIE</i> , 2015, , .	0.8	3

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109	On the inversion in GaAs metal-insulator-semiconductor heterostructures. Applied Physics Letters, 1997, 70, 228-230.	3.3	2
110	Metal Contacts to GaN. Springer Series in Materials Science, 1999, , 191-215.	0.6	2
111	Investigation of Buffer Layers for GaN Grown by MBE. Materials Research Society Symposia Proceedings, 2000, 639, 3171.	0.1	2
112	GaN-Based Modulation-Doped FETs and Heterojunction Bipolar Transistors. , 2006, , 547-626.		2
113	Growth of High-Quality Pb(ZrxTi1-x)O3 Films by Peroxide MBE and Their Optical and Structural Characteristics. Materials Research Society Symposia Proceedings, 2006, 966, 1.	0.1	2
114	Polarization in GaN Based Heterostructures and Heterojunction Field Effect Transistors (HFETs). , 2008, , 373-466.		2
115	Intrinsic Polarization of Self-Assembled Guanosine Supramolecules in GaN-Based Metalâ€Semiconductorâ€Metal Nano-Structures. Journal of Display Technology, 2009, 5, 446-451.	1.2	2
116	Stress test measurements of lattice-matched InAlN/AlN/GaN HFET structures. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1345-1347.	1.8	2
117	Enhancement of optical and structural quality of semipolar (11-22) GaN by introducing nanoporous SiNxinterlayers. , 2015, , .		2
118	Strong carrier localization in stacking faults in semipolar (11-22) GaN. Proceedings of SPIE, 2015, , .	0.8	2
119	Hot-electron noise spectroscopy for HFET channels. , 2017, , .		2
120	New high-speed (Al, Ga) as modulation doped field-effect transistors. IEEE Circuits and Devices: the Magazine of Electronic and Photonic Systems, 1985, 1, 35-38.	0.4	1
121	Investigation of Epitaxially Grown PbO, TiO2 and ZrO2 as Bridge Layers for Integration of PZT on GaN by MBE. Materials Research Society Symposia Proceedings, 2006, 966, 1.	0.1	1
122	On the Light Emission in GaN Based Heterostructures at High Injection. Materials Research Society Symposia Proceedings, 2009, 1202, 23.	0.1	1
123	The effect of barrier strain on the reliability of In<sub>x</sub>/i> Al<sub>1â€x</sub>/i>N/AlN/GaN heterostructure fieldâ€effect transistors. Physica Status Solidi - Rapid Research Letters, 2012, 6, 163-165.	2.4	1
124	Electron energy relaxation in wurtzite ZnO and GaN. , 2013, , .		1
125	Fabrication of Schottky Diodes on Zn-polar BeMgZnO/ZnO Heterostructure Grown by Plasma-assisted Molecular Beam Epitaxy. Journal of Visualized Experiments, 2018, , .	0.3	1
126	Electronic Band Structure of Bulk and QW Nitrides. Springer Series in Materials Science, 1999, , 45-82.	0.6	1



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127	Electrical properties of BeMgZnO/ZnO heterostructures with high-density two-dimensional electron gas. , 2019, , .		1
128	Microcalorimetric absorption spectroscopy in GaN/AlGaIn quantum wells. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 59, 319-322.	3.5	0
129	Optical Processes in Nitride Semiconductors. Springer Series in Materials Science, 1999, , 295-339.	0.6	0
130	Bowing Parameter of Al <sub>x</sub> Ga <sub>1-x</sub> N. Materials Research Society Symposia Proceedings, 2002, 722, 321.	0.1	0
131	Epitaxy of highly optical efficient GaN on O and Zn face ZnO. Materials Research Society Symposia Proceedings, 2003, 798, 748.	0.1	0
132	Growth Structure, and Optical Properties of III-Nitride Quantum Dots. Materials Research Society Symposia Proceedings, 2003, 799, 257.	0.1	0
133	Growth Structure, and Optical Properties of III-Nitride Quantum Dots. Materials Research Society Symposia Proceedings, 2003, 789, 334.	0.1	0
134	Growth Structure, and Optical Properties of III-Nitride Quantum Dots. Materials Research Society Symposia Proceedings, 2003, 794, 177.	0.1	0
135	Epitaxial Growth of ZrO <sub>2</sub> on GaN by MOMBE for High Dielectric Material Applications. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
136	III-V Nitrides and Silicon Carbide as Optoelectronic Materials. , 2006, , 4-1-4-59.		0
137	Electrical Characterization of Isotype n-ZnO/n-GaN Heterostructures. Materials Research Society Symposia Proceedings, 2006, 957, 1.	0.1	0
138	Persistent Photoconductivity in High-mobility Al <sub>x</sub> Ga <sub>1-x</sub> N/AlN/GaN Heterostructures Grown by Metal-organic Vapor-phase Epitaxy. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
139	Transport Properties and Conduction Band Offset of n-ZnO/n-6H-SiC Heterostructures. Materials Research Society Symposia Proceedings, 2006, 957, 1.	0.1	0
140	Schottky I-V Characteristics of Au/Ni/GaN/SiN <sub>x</sub> nanonetwork/sapphire structures. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
141	1.37 - 2.90 Micron Intersubband Transitions in GaN/AlN Superlattices. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
142	Comparative Study of Thin PZT Sol-gel Films Deposited on Pt and GaN Substrates. Materials Research Society Symposia Proceedings, 2007, 1034, 152.	0.1	0
143	A General Nonlithographic Method for Producing Nanodots by RIE Etching. Materials Research Society Symposia Proceedings, 2007, 1059, 1.	0.1	0
144	Hydrostatic Pressure Studies of GaN/AlGaIn/GaN Heterostructure Devices with Varying AlGaIn Thickness and Composition. Materials Research Society Symposia Proceedings, 2007, 994, 1.	0.1	0

#	ARTICLE	IF	CITATIONS
145	Effect of Growth Conditions on Defect-related Photoluminescence in ZnO Thin Films Grown by Plasma Assisted MBE. Materials Research Society Symposia Proceedings, 2007, 1035, 1.	0.1	0
146	Blue and Yellow Luminescence in ZnO Films Grown by Peroxide MBE. Materials Research Society Symposia Proceedings, 2007, 1035, 1.	0.1	0
147	Photoelectrochemical Etching of GaN Thin Films With Varying Carrier Concentrations. Materials Research Society Symposia Proceedings, 2007, 1040, 1.	0.1	0
148	Appendix: Periodic Table of Pertinent Elements. , 0, , 847-847.		0
149	Determination of Impurity and Carrier Concentrations. , 0, , 121-163.		0
150	Estimation of carrier leakage in InGaN light emitting diodes from photocurrent measurements. Proceedings of SPIE, 2014, , .	0.8	0
151	GROWTH OF III-NITRIDE SEMICONDUCTORS AND THEIR CHARACTERIZATION. , 2003, , 1-124.		0
152	Modulation Doped FETs. , 0, , .		0
153	Self-Assembled Guanosine-Based Nanoscale Molecular Photonic Devices. , 2010, , 77-99.		0
154	LATTICE-MISMATCHED HETEROEPITAXY. , 1995, , 145-209.		0